

AMENDMENT TO THE CLAIMS:

1. (Currently Amended) A reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:
a display electrode made of a reflective material for reflecting the incident light on a surface thereof;
a back-surface electrode disposed in contact with a back surface of the display electrode; and
a transistor for controlling current to the display electrode, said back-surface electrode and the transistor being electrically interconnected,
wherein said transistor is a thin-film transistor which has an active layer, and a portion of the back-surface electrode is directly connected to said active layer via a contact hole,
wherein said display electrode and said back-surface electrode are patterned into the same shape, and
a thickness of said back-surface electrode is such that no substantial protrusion is formed in said display electrode and said thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å.

2. (Original) The device according to claim 1, wherein
said back-surface electrode is made of a high melting point metal.

3. (Original) The device according to claim 2, wherein
said display electrode is made of aluminum.

4. (Canceled)

5. (Canceled)

6. (Previously Presented) The device according to claim 1, wherein said active layer is a polycrystalline silicon layer.

7. (Original) The device according to claim 6, wherein
said back-surface electrode is made of a high melting point metal.

8. (Currently Amended) ~~The~~ A method of manufacturing a reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:

a step of forming a back-surface electrode layer, a thickness of said back-surface electrode layer is such that no substantial protrusion is formed in said display electrode and said thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å;

a step of forming a display electrode layer constituted of a reflective material on the back-surface electrode layer; and

a step of patterning the formed back-surface electrode layer and the display electrode layer to form a surface electrode and a back-surface electrode in the same shape,

to form a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode.

9. (Original) The method according to claim 8, further comprising:

a process of forming a thin film transistor as an active layer of polycrystalline silicon on a substrate;

a step of forming an insulating film to cover the thin film transistor; and

a step of forming a contact hole in the insulating film, wherein

said back-surface electrode is formed on a smoothed film with said contact hole formed therein.

10. (Previously Presented) The method of manufacturing a reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side comprising:

a step of forming a back-surface electrode layer;

a step of forming a display electrode layer constituted of a reflective material on the back-surface electrode layer;

a step of patterning the formed back-surface electrode layer and the display electrode layer to form a surface electrode and a back-surface electrode in the same shape;

to form a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode;

a process of forming a thin film transistor as an active layer of polycrystalline silicon on a substrate;

a step of forming an insulating film to cover the thin film transistor; and

a step of forming a contact hole in the insulating film, wherein

said back-surface electrode is formed on a smoothed film with said contact hole formed therein, wherein

said back-surface electrode is made of a high melting point metal.

11. (Original) The method according to claim 10, wherein

said high melting point metal is selected from the group consisting of molybdenum, titanium, tungsten, tantalum and chromium, or an alloy thereof.

12. (Previously Presented) The device according to claim 1, wherein a part of the back-surface electrode elongates to a place above a part of the active layer and the contact hole is formed between the one end portion of the back-surface electrode and the part of the active layer.

13. (Currently Amended) A reflective type liquid crystal display device comprising:
a back-surface electrode layer;

a display electrode layer is constituted of a reflective material on the back-surface electrode layer;

a back-surface electrode layer and the display electrode layer are patterned to form a surface electrode and a back-surface electrode in the same shape;

a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode;

a thin film transistor is formed as an active layer of polycrystalline silicon on a substrate;

an insulating layer is formed to cover the thin film transistor; and

a contact hole is formed in the insulating film, wherein

said back-surface electrode is formed on a smoothed film with said contact hole formed therein, wherein

said back-surface electrode is made of a high melting point metal, and

a thickness of said back-surface electrode is greater than 200 Å and less than or equal to 1500 Å.

14. (Previously Presented) The device according to claim 1, wherein the back-surface electrode is made of a non-oxide metal.

15. (Previously Presented) The device according to claim 2, wherein

said high melting point metal is selected from the group consisting of molybdenum, titanium, tungsten, tantalum and chromium, or an alloy thereof.

16. (New) A reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:

a display electrode made of a reflective material for reflecting the incident light on a surface thereof;

a back-surface electrode disposed in contact with a back surface of the display electrode; and

a transistor for controlling current to the display electrode, said back-surface electrode

and the transistor being electrically interconnected,

wherein said transistor is a thin-film transistor which has an active layer, and a portion of the back-surface electrode is directly connected to said active layer via a contact hole,

wherein said display electrode and said back-surface electrode are patterned into the same shape, and

a thickness of said back-surface electrode is such that no substantial protrusion is formed in said display electrode, and

said back-surface electrode is made of titanium, said display electrode is made of aluminum, and said display electrode is in (111) orientation state.

17. (New) The device according to claim 16, wherein said active layer is a polycrystalline silicon layer.

18. (New) The device according to claim 16, wherein a part of the back-surface electrode elongates to a place above a part of the active layer and the contact hole is formed between the one end portion of the back-surface electrode and the part of the active layer.

19. (New) A method of manufacturing a reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:

a step of forming a back-surface electrode layer, a thickness of said back-surface electrode layer is such that no substantial protrusion is formed in said display electrode, said back-surface electrode layer is made of titanium;

a step of forming a display electrode layer constituted of a reflective material on the back-surface electrode layer, said display electrode layer is made of aluminum, said display electrode layer is in (111) orientation state; and

a step of patterning the formed back-surface electrode layer and the display electrode layer to form a surface electrode and a back-surface electrode in the same shape,

to form a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode.

20. (New) The method according to claim 19, further comprising:

a process of forming a thin film transistor as an active layer of polycrystalline silicon on a substrate;

a step of forming an insulating film to cover the thin film transistor; and

a step of forming a contact hole in the insulating film, wherein

said back-surface electrode is formed on a smoothed film with said contact hole

formed therein.

21. (New) A reflective type liquid crystal display device comprising:

a back-surface electrode layer;

a display electrode layer is constituted of a reflective material on the back-surface electrode layer;

a back-surface electrode layer and the display electrode layer are patterned to form a surface electrode and a back-surface electrode in the same shape;

a display electrode for reflecting the incident light by a surface thereof and the back-surface electrode disposed in contact with a back surface of the display electrode;

a thin film transistor is formed as an active layer of polycrystalline silicon on a substrate;

an insulating layer is formed to cover the thin film transistor; and

a contact hole is formed in the insulating film, wherein

said back-surface electrode is formed on a smoothed film with said contact hole formed therein, and

said back-surface electrode is made of a titanium, said display electrode is made of aluminum, and said display electrode is in (111) orientation state.